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SISS61DN-T1-GE3-VB Datasheet

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 20	0.0040 at V_{GS} = 10 V	- 52	21.5 nC
	0.0060 at V_{GS} = 4.5 V	- 40	

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

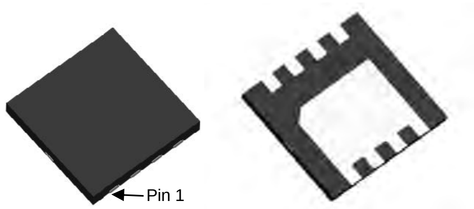
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

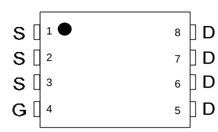
- Load Switch
- Adaptor/Battery Switch

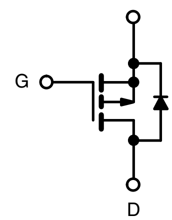
DFN 3x3 EP

Top View   Bottom View



Top View





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 20	V
Gate-Source Voltage		V_{GS}	± 16	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 52	A
	T_C = 70 °C		- 40[g]	
	T_A = 25 °C		- 26[b, c]	
	T_A = 70 °C		- 21[b, c]	
Pulsed Drain Current		I_{DM}	- 150	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 40[g]	
	T_A = 25 °C		- 4.5[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	54	W
	T_C = 70 °C		34.7	
	T_A = 25 °C		5.0[b, c]	
	T_A = 70 °C		3.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)[d, e]			260	

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, f]	t ≤ 10 s	R_{thJA}	20	25	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.8	2.3	

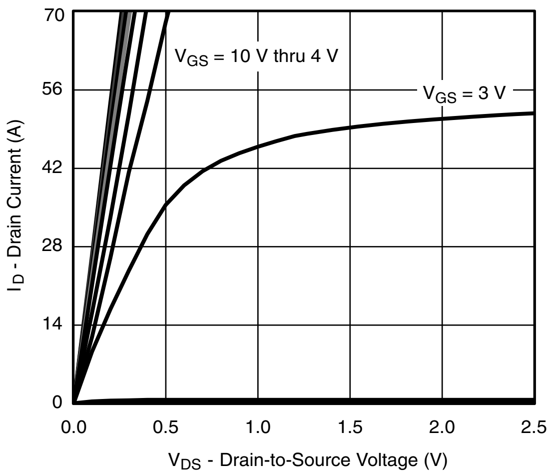
Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 10 s.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = - 250 µA	- 20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 15		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			4.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1		- 2.2	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≤ - 5 V, V_{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 26 A		0.0040		Ω
		V_{GS} = - 4.5 V, I_D = - 21 A		0.0060		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 26 A		58		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 10 V, V_{GS} = 0 V, f = 1 MHz		4595		pF
Output Capacitance	C_{oss}			910		
Reverse Transfer Capacitance	C_{rss}			813		
Total Gate Charge	Q_g	V_{DS} = - 10 V, V_{GS} = - 10 V, I_D = - 20 A		95.3	143	nC
		V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 20 A		46.5	70	
Gate-Source Charge	Q_{gs}			13.7		
Gate-Drain Charge	Q_{gd}			12.5		
Gate Resistance	R_g	f = 1 MHz	0.4	1.9	3.8	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 1 Ω I_D ≅ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω		19	30	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			65	98	
Fall Time	t_f			13	20	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 1 Ω I_D ≅ - 10 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		55	83	
Rise Time	t_r			52	78	
Turn-Off Delay Time	$t_{d(off)}$			53	80	
Fall Time	t_f			25	38	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 40	A
Pulse Diode Forward Current[a]	I_{SM}				- 70	
Body Diode Voltage	V_{SD}	I_S = - 1 A		- 0.74	- 1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 10 A, dI/dt = 100 A/µs, T_J = 25 °C		42	63	ns
Body Diode Reverse Recovery Charge	Q_{rr}			25	38	nC
Reverse Recovery Fall Time	t_a			12		ns
Reverse Recovery Rise Time	t_b			30		

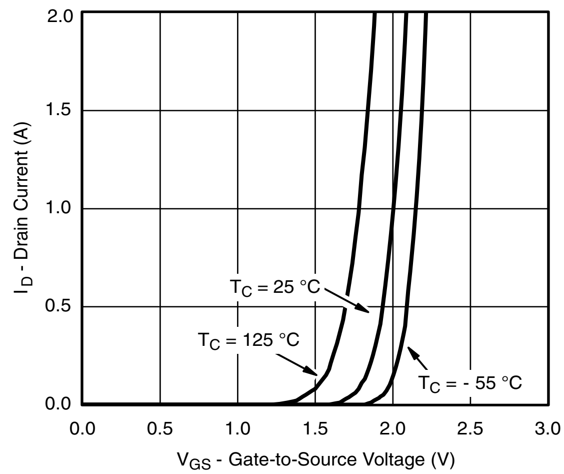
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

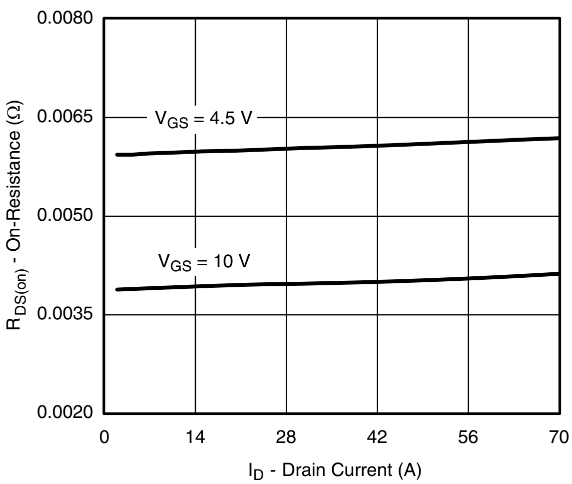
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



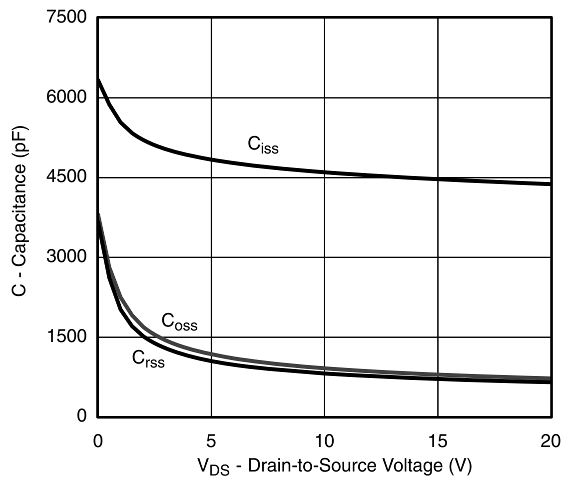
Output Characteristics



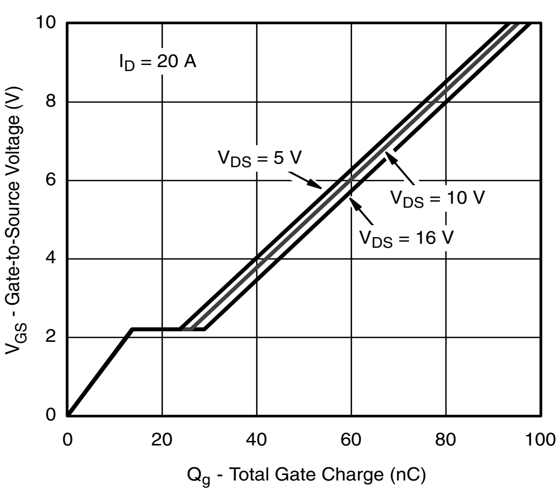
Transfer Characteristics



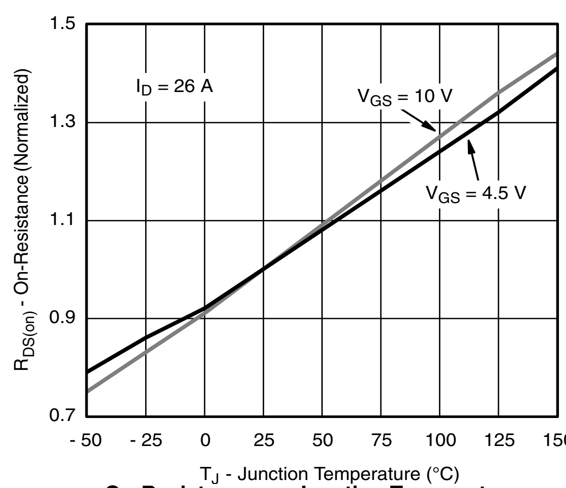
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

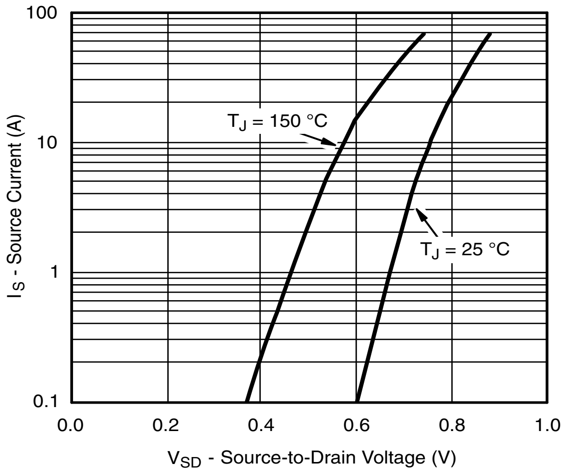


Gate Charge

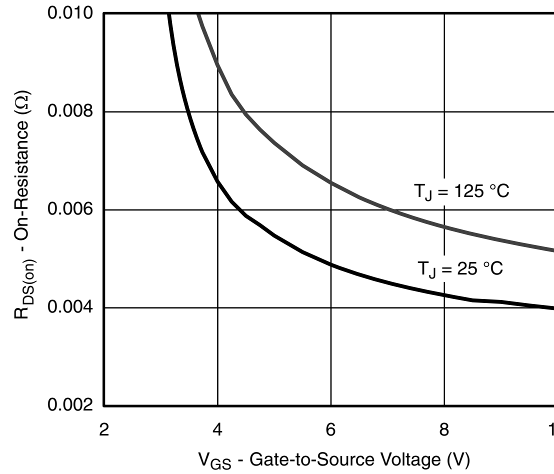


On-Resistance vs. Junction Temperature

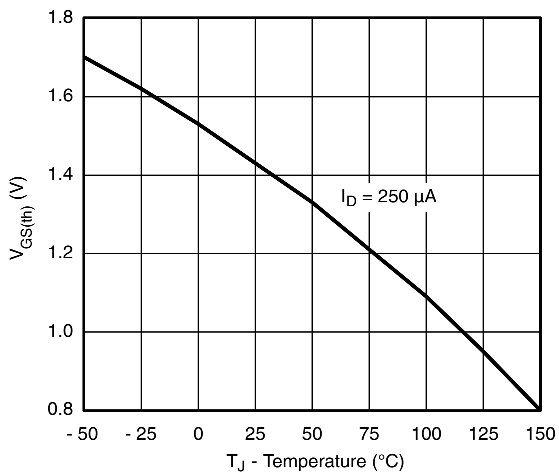
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



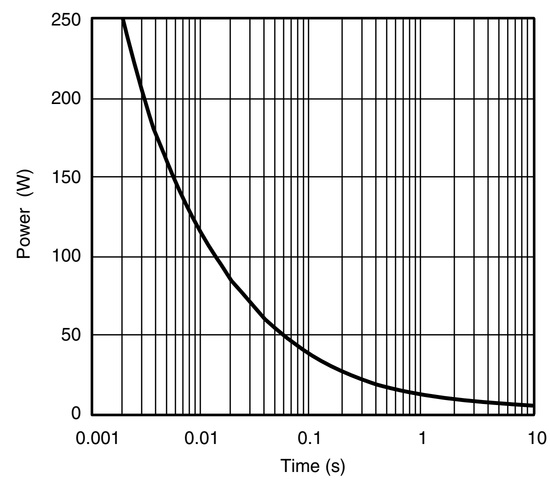
Source-Drain Diode Forward Voltage



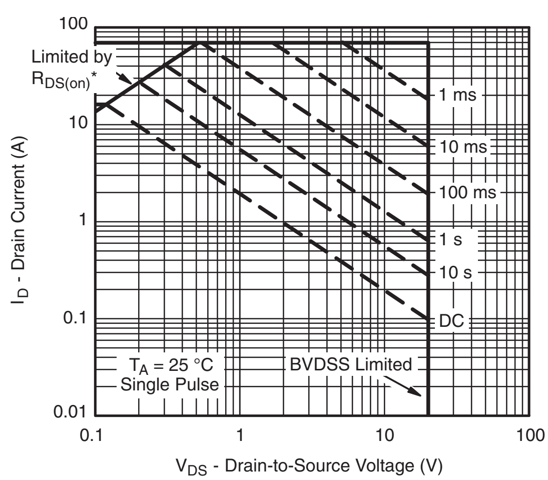
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



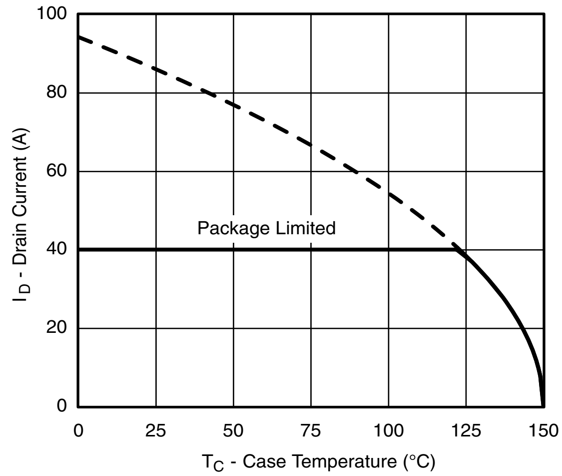
Single Pulse Power, Junction-to-Ambient



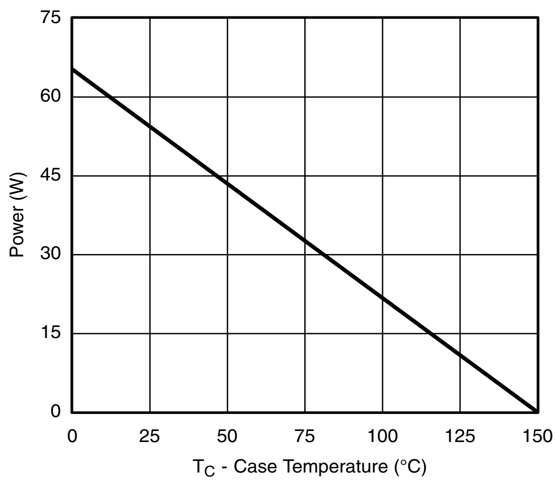
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

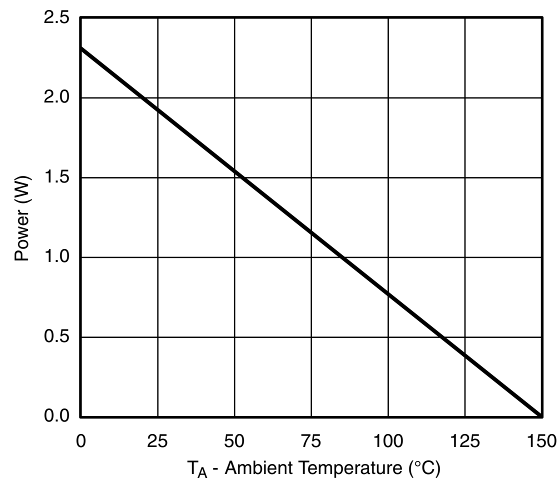
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



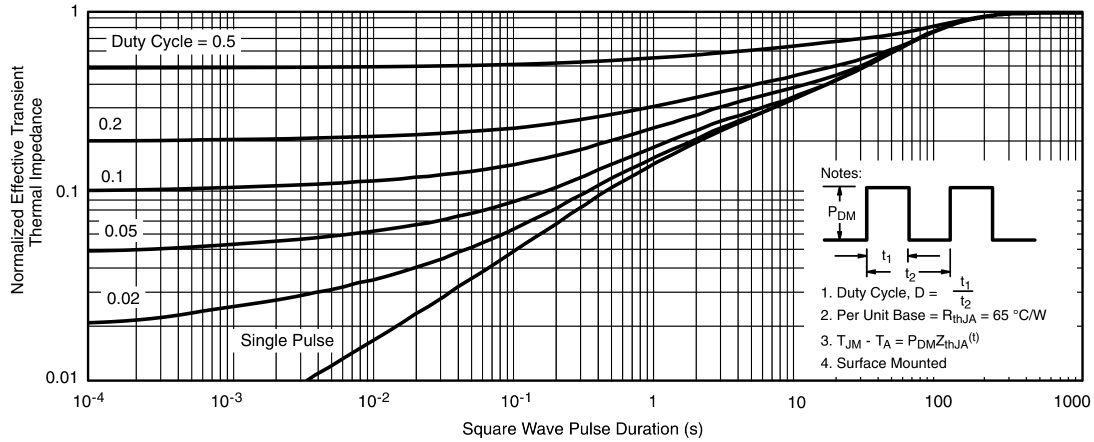
Power, Junction-to-Case



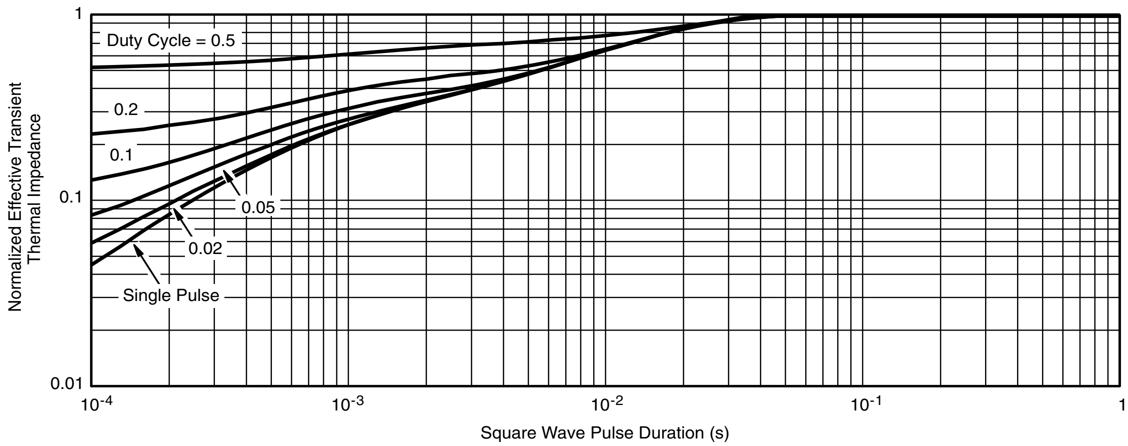
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

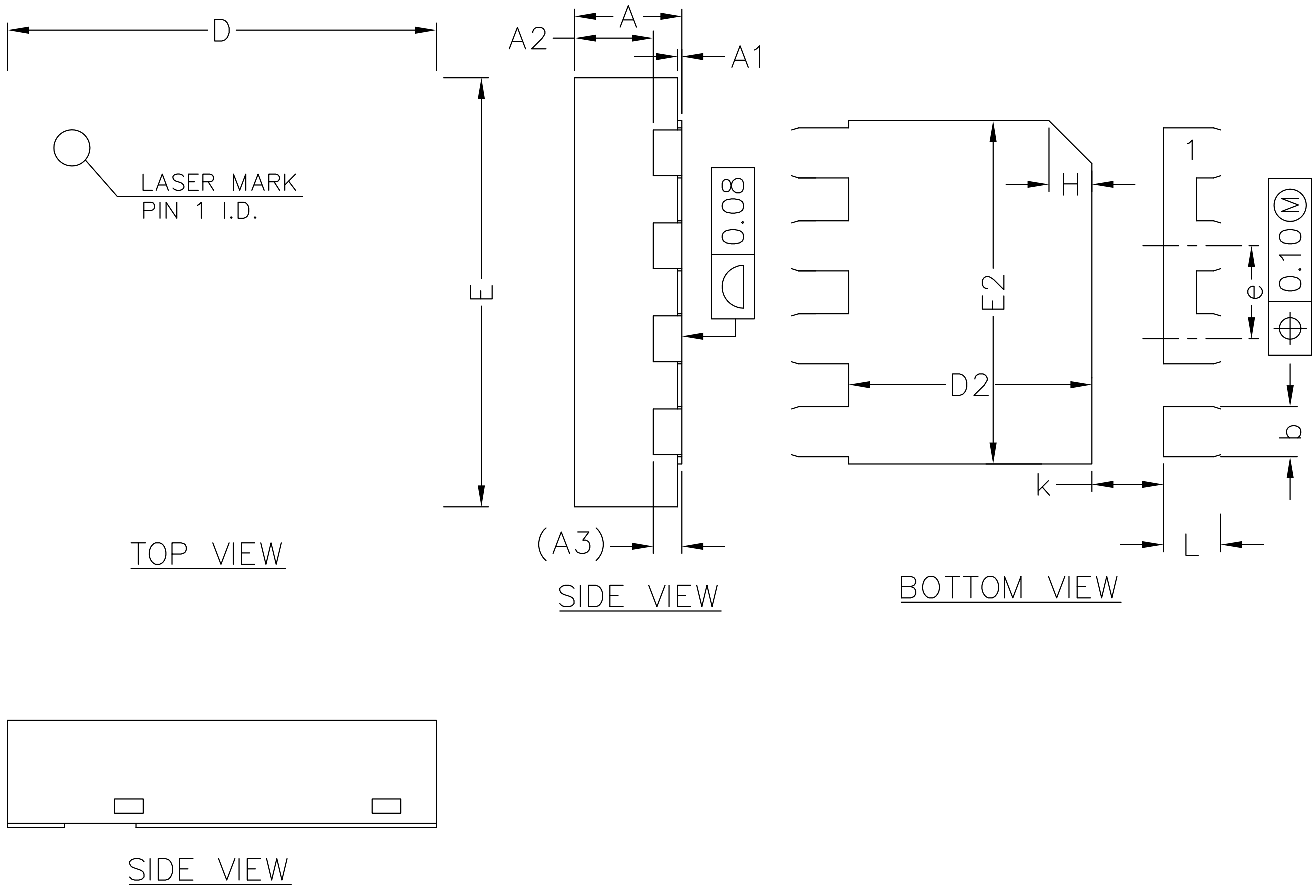
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.50	0.55	0.60
A3	0.20REF		
b	0.30	0.35	0.40
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.60	1.70	1.80
E2	2.30	2.40	2.50
e	0.55	0.65	0.75
K	0.40	0.50	0.60
L	0.35	0.40	0.45

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